

General Description

The MY125N06NE5 uses Split Gate Trench MOSFET technology for Excellent package for heat dissipation and High density cell design for low Ros(ON)

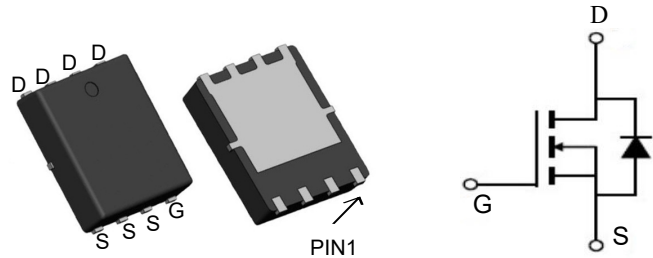


Features

V_{DSS}	60	V
I_D	125	A
$P_D(T_C=25^\circ\text{C})$	113	W
$R_{DS(ON)}(at V_{GS}=10V)$	2.4	m Ω

Application

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY125N06NE5	PDFN5*6-8L	MY125N06NE5	5000

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	120	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	67	A
I_{DM}	Pulsed Drain Current ²	250	A
EAS	Single Pulse Avalanche Energy ³	151	mJ
I_{AS}	Avalanche Current	55	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	48	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	50	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.6	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	1.8	2.2	mΩ
		V _{GS} =4.5V, I _D =20A	---	2.5	3.6	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25 °C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55 °C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	91	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =10V, I _D =20A	---	21	---	nC
Q _{gs}	Gate-Source Charge		---	12.5	---	
Q _{gd}	Gate-Drain Charge		---	14.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =20A	---	12	---	ns
T _r	Rise Time		---	6	---	
T _{d(off)}	Turn-Off Delay Time		---	38.5	---	
T _f	Fall Time		---	11.5	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3032	---	pF
C _{oss}	Output Capacitance		---	1588	---	
C _{rss}	Reverse Transfer Capacitance		---	207	---	
I _s	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	85	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25 °C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=55A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.

Typical Characteristics

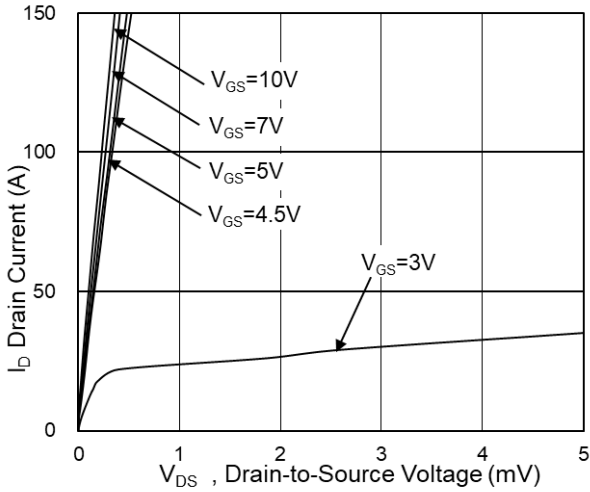


Fig.1 Typical Output Characteristics

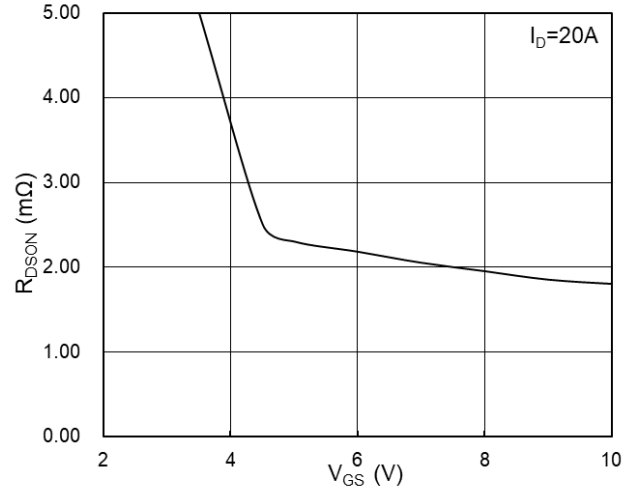


Fig.2 On-Resistance vs G-S Voltage

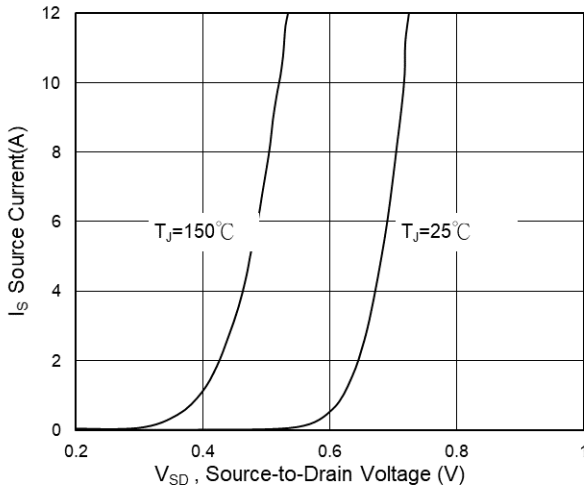


Fig.3 Source Drain Forward Characteristics

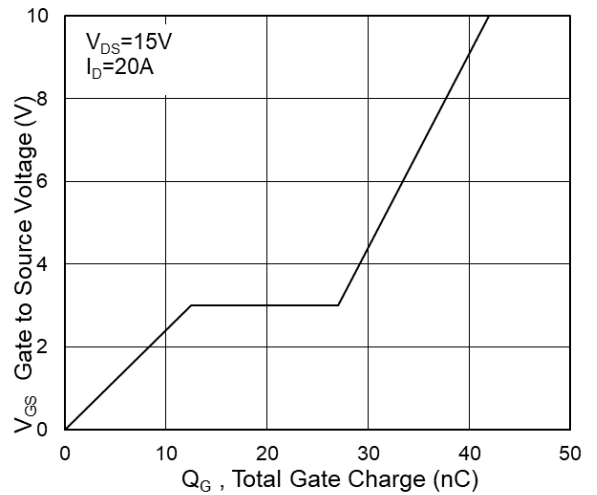


Fig.4 Gate-Charge Characteristics

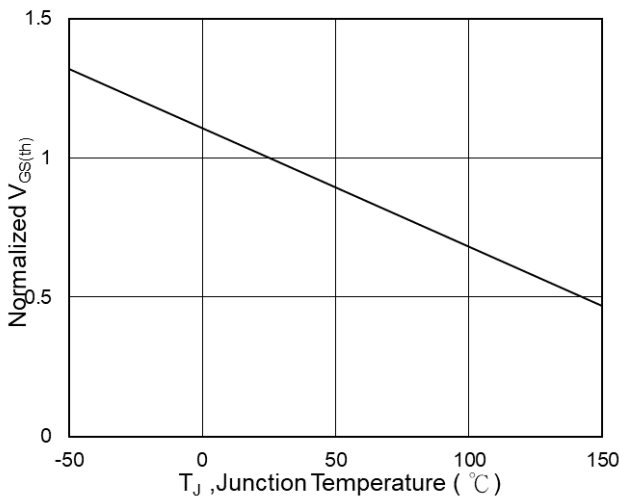


Fig.5 Normalized $V_{GS(th)}$ vs T_J

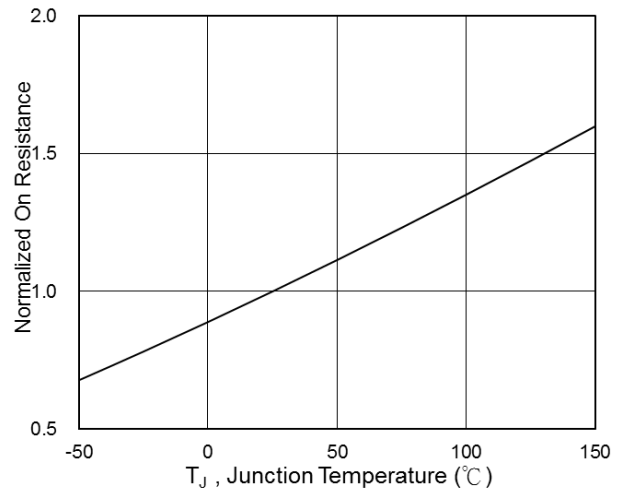


Fig.6 Normalized $R_{DS(on)}$ vs T_J

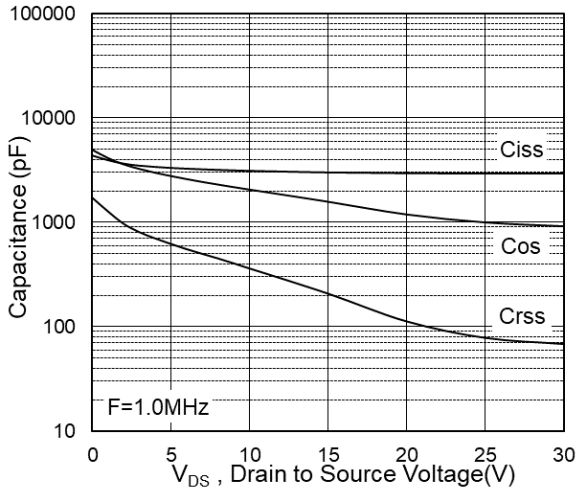


Fig.7 Capacitance

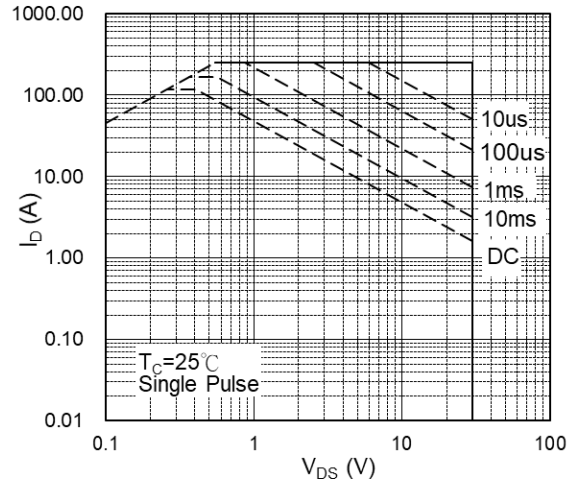


Fig.8 Safe Operating Area

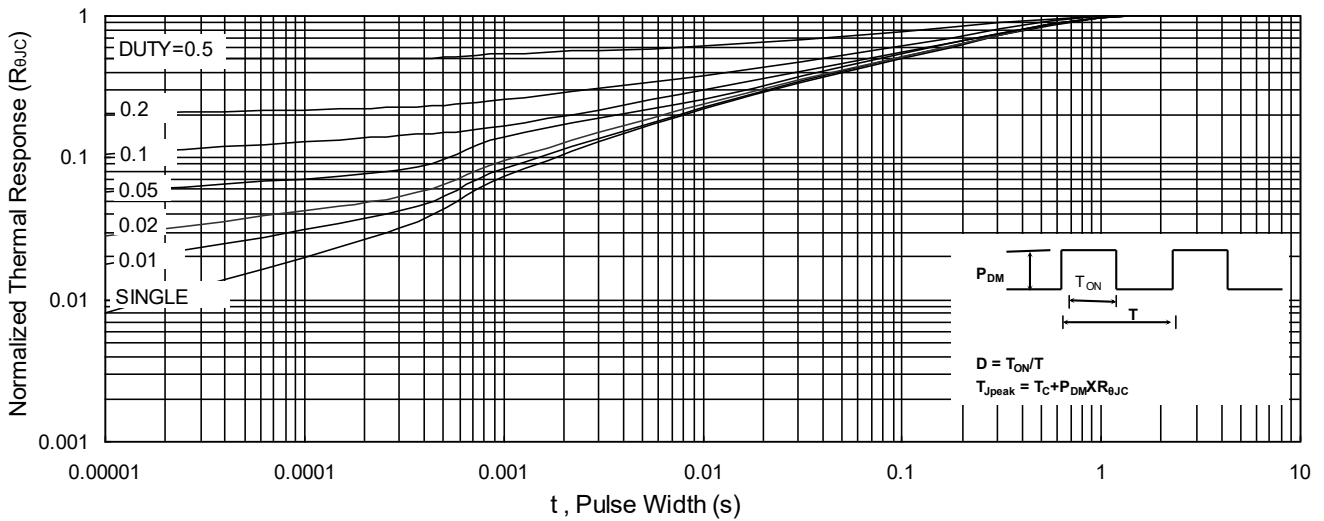


Fig.9 Normalized Maximum Transient Thermal Impedance

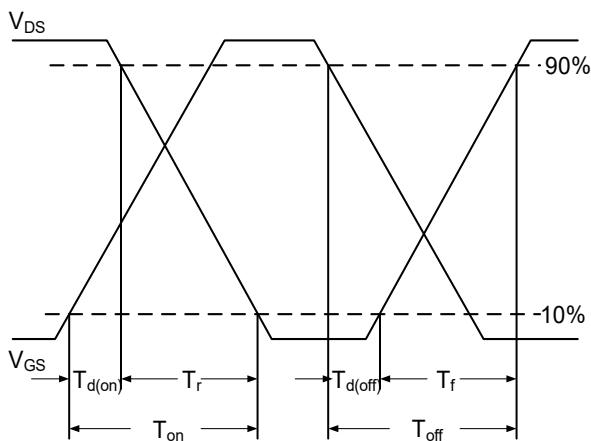


Fig.10 Switching Time Waveform

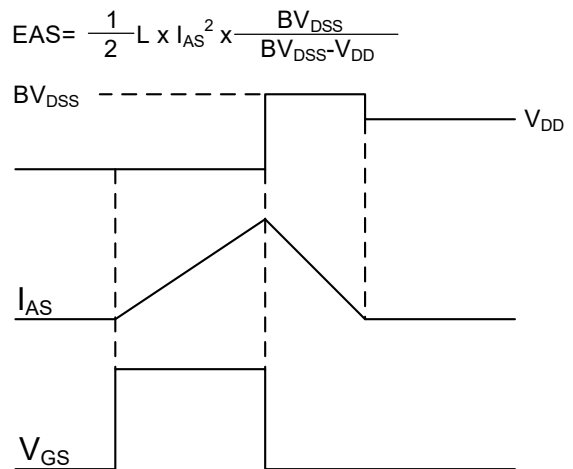
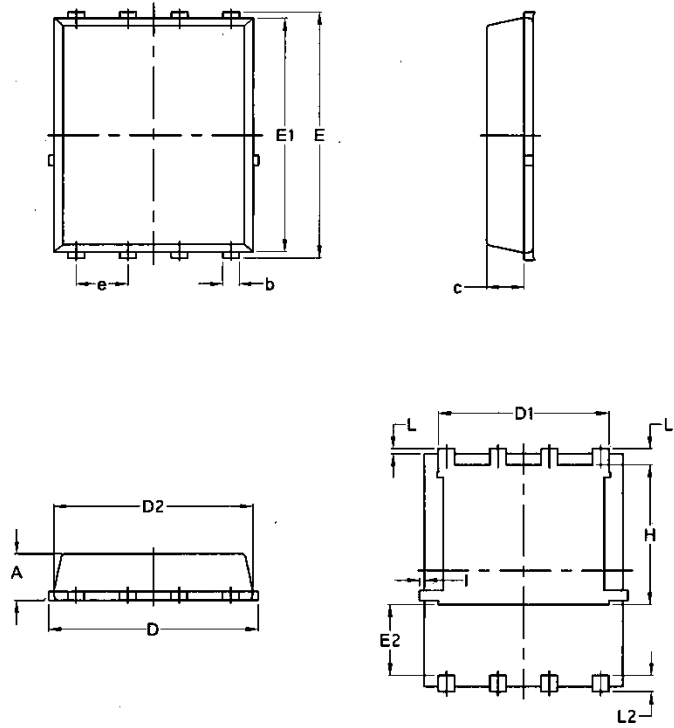


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-DFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070